

Q1  
current - drain voltage characteristic or the like. In order to suppress the floating-body effect, an isolation oxide film (partial oxide film) is formed in an upper layer portion so as not to come in contact with the buried oxide film and constitutes a partial isolation region together with a part of an SOI layer in a lower layer portion and a body terminal is provided in a body region formed in a region isolated in the partial isolation region. Consequently, a partial isolation technique capable of fixing a substrate potential (body potential) through the SOI layer provided under the partial oxide film is effective. However, there is a problem in that the partial isolation technique does not have the latch up free which is the advantage of the complete isolation technique.

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Please amend the specification at page 18, line 22 through page 19, line 1 as shown below:

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Q2  
Moreover, a body region 10 (a body region outside an element formation region) is isolated by the partial oxide film 31 and the p well region 11 provided thereunder and is formed from the surface of the SOI layer 4 to the back face thereof. The body region 10 is electrically connected to a main part of the body region to be the SOI layer 4 provided under the gate electrode 7 through the p well region 11.

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IN THE CLAIMS

Please cancel Claim 2 without prejudice or disclaimer.

Please amend Claims 1 and 3-6 as shown in clean form below:

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Q3  
1. (Amended) A semiconductor device having an SOI structure including a semiconductor substrate, a buried insulating layer and an SOI layer, comprising:  
a MOS transistor provided in an element formation region of said SOI layer; and  
a partial isolation region provided in said SOI layer and serving to isolate said